

650 V enhancement mode GaN high-power density half-bridge with high-voltage driver



QFN 9 x 9 x 1 mm



Product status link

[GANSPIN611](#)

Features

- Power system-in-package family integrating high-voltage GaN transistors in half-bridge configuration with high-voltage gate driver:
 - $R_{DS(ON)} = 138 \text{ m}\Omega$
 - $I_{DS(MAX)} = 10 \text{ A}$
- Reverse conduction capability and zero reverse recovery loss
- 10 V/ns typ. output dV/dt in both hard-on and hard-off, tailored for motor control
- Externally adjustable turn-on dV/dt
- Linear regulators to regulate high-side and low-side driver supply voltage
- Internal bootstrap diode
- Comparator for overcurrent detection with Smart Shutdown function
- UVLO protection on VCC, V_{HS} and V_{LS}
- Interlocking function, shutdown, standby and fault pins
- 55 ns gate driver leading to overall 150 ns typ. output propagation delay
- 3.3 V to 20 V compatible inputs with hysteresis and pull-down

Applications

- Home appliances
- Compressors
- Pumps
- Fans
- Personal care appliances
- Factory automation
- Servo drives
- Power tools

Description

GaN-based motion control is the focus of the GaNSPIN platform. Unlike many general-purpose solutions or those tailored for power conversion, the GaNSPIN series is specifically engineered to meet the peculiar demands of motion control systems.

The **GANSPIN611** is an advanced power system-in-package integrating two enhancement mode GaN transistors in half-bridge configuration driven by a state-of-the-art high-voltage, high-frequency gate driver.

The integrated power GaNs have $R_{DS(ON)}$ of 138 m Ω and 650 V drain source breakdown voltage, while the high-side of the embedded gate driver can be easily supplied by the integrated bootstrap diode.

The GANSPIN611, being designed for motion control, optimizes the output dV/dt to 10 V/ns typ. for both hard-on and hard-off. This is required in motor control for EMI, motor winding, and ball bearing reliability.

Robustness and reliability are also distinctive factors of the GaNSPIN series. Embedding advanced protections, GaNSPIN devices ensure the best possible system robustness. SmartShutdown overcurrent protection delivers the fastest response possible thanks to embedded logic and dedicated fast comparators.

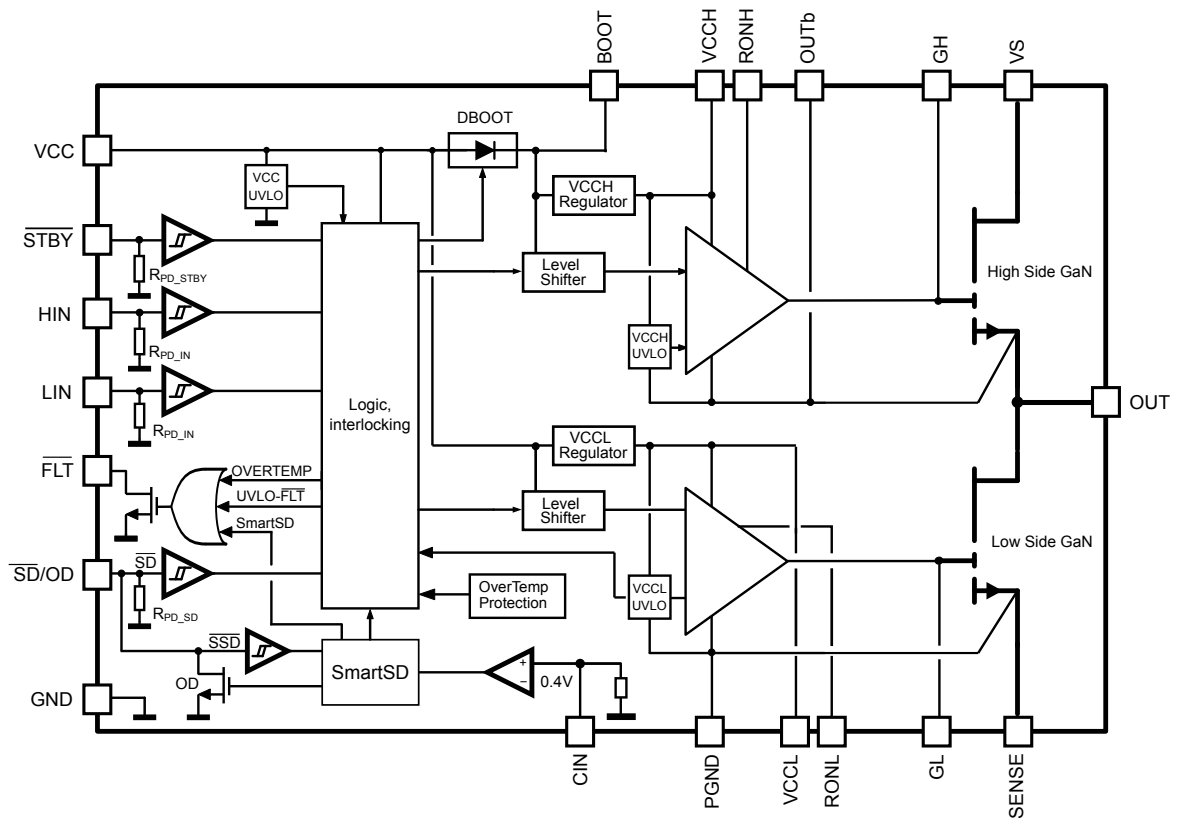
The GANSPIN series also features linear regulators on both the lower and upper driving sections, preventing the power switches from operating in low efficiency or dangerous conditions, and the interlocking function avoids cross-conduction conditions. The UVLO is fine-tuned for motion control for optimal performances.

The GANSPIN611 is available in a compact 9x9x1 mm QFN package and operates in the industrial temperature range, -40 °C to 125 °C.

The GaNSPIN611 is pin-to-pin with GaNSPIN612 ($R_{DS(ON)}$ of 270 mΩ) to maximize scalability in a platform approach.

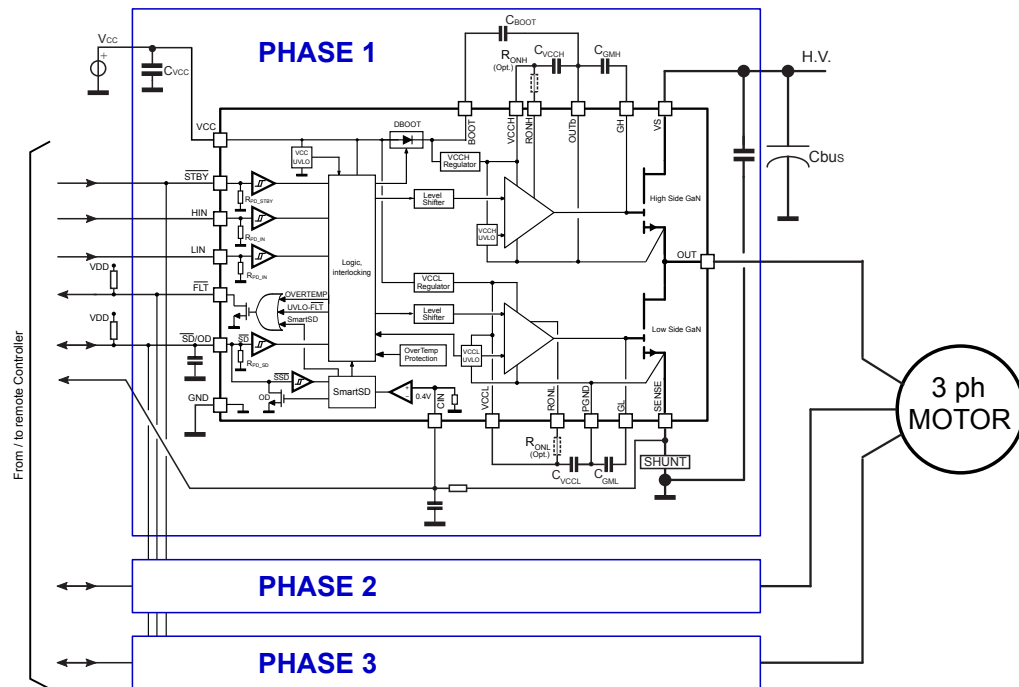
1 Block diagram

Figure 1. GANSPIN611 block diagram



2 Typical application schematic

Figure 2. Typical motor control application schematic



3 Pin descriptions

Figure 3. GANSPIN611 pin connections

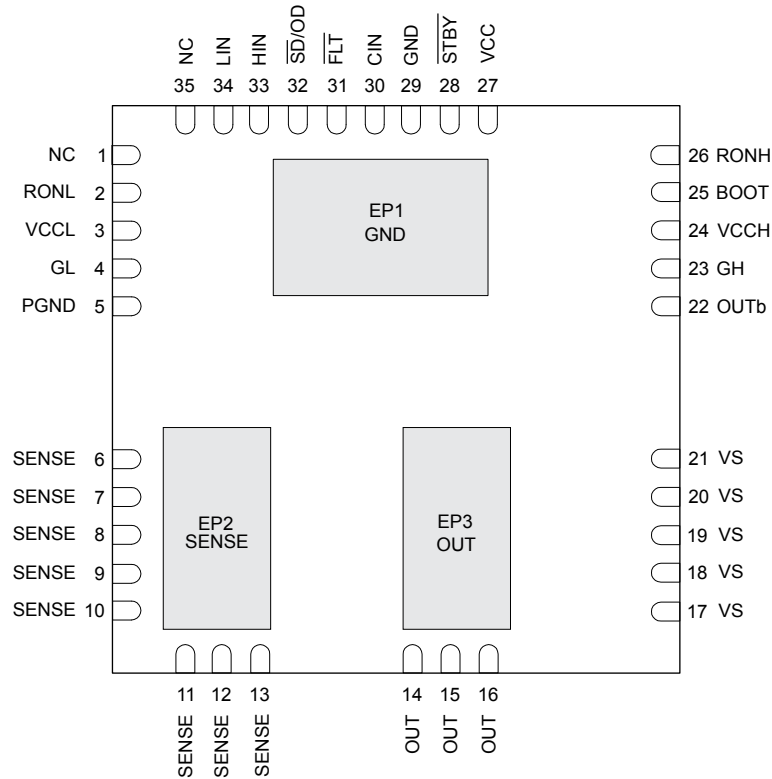


Table 1. GANSPIN611 pin list

Pin N.	Name	Type	Function
1, 35	NC	-	Not connected pin. The pins can be either connected to GND or left floating.
2	RONL	Output	A resistor connected between this pin and VCCL sets the turn-on resistor of the low-side driver. Mounting the resistor as close as possible to the RONL pin optimizes the operation of the driver. It is possible to drive the GaN with minimum internal resistance connecting the RONL pin to VCCL pin.
3	VCCL	Power	Output of the linear regulator that supplies the output stage of the low-side driver. A ceramic capacitor of 47 nF min. (X7R, 16 V) must be placed as close as possible between this pin and PGND.
4	GL	Output	Gate of low-side GaN transistor. Add 680 pF capacitor to PGND.
5	PGND	Power	Reference potential of low-side driver and relevant external components (VCCL capacitor and components connected to GL). This pin is internally connected to the low-side GaN transistor source.
6 to 13, EP2	SENSE	Power	Source of low-side GaN transistor. The exposed pad has both an electrical and thermal purpose: low-side transistor power losses are dissipated soldering EP2 to proper copper area.
14, 15, 16, EP3	OUT	Power	Middle point of half-bridge. The exposed pad has both an electrical and thermal purpose: high-side transistor power losses are dissipated soldering EP3 to proper copper area.
17 to 21	VS	Power	Drain of high-side GaN transistor.
22	OUTb	Power	Reference potential of high-side driver and relevant external components (BOOT capacitor, VCCH capacitor, and components connected to GH). This pin is internally connected to the high-side GaN transistor source.

Pin N.	Name	Type	Function
23	GH	Output	Gate of the high-side GaN transistor. Add 680 pF capacitor to OUTb.
24	VCCH	Power	Output of the linear regulator that supplies the output stage of the high-side driver. A ceramic capacitor of 47 nF min. (X7R, 16 V) must be placed as close as possible between this pin and OUTb.
25	BOOT	Power	Supply voltage of high-side floating driver. A ceramic capacitor equal or greater than C_{VCCH} (X7R, 50 V) must be placed as close as possible between this pin and OUTb. The input of the high-side driver regulator is internally connected to this pin.
26	RONH	Output	A resistor connected between this pin and VCCH sets the turn-on resistor of the high-side driver. Mounting the resistor as close as possible to the RONH pin optimizes the operation of the driver. It is possible to drive the GaN with minimum internal resistance connecting the RONH pin to VCCH pin.
27	VCC	Power	Supply voltage of logic section. A small bypass capacitor (100 nF typ.) very close to the pin is required to get a clean bias voltage for the signal part of the IC. The large bulk capacitor that is normally used to supply the controller is sufficient to also supply GANSPIN611: if not present, a value equal or larger than 2.2 μ F is suggested. The input of the low-side driver regulator is internally connected to this pin.
28	$\overline{\text{STBY}}$	Input	Standby mode activation pin. Setting this pin to GND, the IC enters a low consumption mode to facilitate the design of low consumption topologies. The internal pull-down resistor is there to avoid uncertain voltage application when IC is not biased. Connect this pin to VCC if standby function is not used.
29, EP1	GND	Power	Ground pin. Common potential of the logic section of the device. The exposed pad has both an electrical and thermal purpose: power dissipation of linear regulators, drivers, and level shifter units can be dissipated soldering EP1 to proper copper area.
30	CIN	Input	Comparator input pin for smartSD. In case of triggering, both GaN are immediately turned off and $\overline{\text{SD/OD}}$ is pulled low. The shunt voltage filtering capacitor shall be placed near CIN pin and on the PCB side of the IC to maximize noise immunity. Connect to GND if not used.
31	FLT	Output	Fault signaling pin. An open-drain MOSFET is turned on to pull the pin down when UVLO, standby, comparator, or overtemperature protection are active. Connect to GND if not used.
32	$\overline{\text{SD/OD}}$	Input	Shutdown input (active low) / open-drain output for comparator with smartSD. When this pin is pulled to GND, the IC immediately interrupts the switching activity defined by LIN and HIN. When CIN exceeds the threshold, smartSD interrupts the switching activity and pulls low the $\overline{\text{SD/OD}}$ pin. Once the overcurrent has ended, the open-drain is released. The internal pull-down resistor is there to avoid uncertain voltage application when IC is not biased.
33	HIN	Input	High-side logic input pin. Driving pulses to control the high-side switch can be applied to this pin. Schmitt trigger input, 20 V tolerant, buffers the input signal before driving level shifters.
34	LIN	Input	Low-side logic input pin. Driving pulses to control the low-side switch can be applied to this pin. Schmitt trigger input, 20 V tolerant, buffers the input signal before driving level shifters.

4 Electrical data

4.1 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in Table 2 may cause permanent damage to the device. Exposure to maximum rating conditions for extended periods may affect device reliability. All voltages referred to ground pins unless otherwise specified.

Table 2. Absolute maximum ratings

Symbol	Parameter	Test condition	Value	Unit
V _{VS-OUT}	High-side GaN Drain-to-Source blocking voltage	T _J = 25 °C, OUT = GND, DC voltage, I _{VS} < 20 µA	650	V
		t _{PULSE} < 100 ns ⁽¹⁾	750	V
I _D	Drain current (per GaN transistor)	DC @ T _{CB} = 25 °C ^{(1) (2)}	9.7	A
		DC @ T _{CB} = 100 °C ^{(1) (2)}	6.4	A
		Peak @ T _{CB} = 25 °C ^{(1) (2) (3)}	16	A
V _{CC}	Logic supply voltage		-0.3 to 21	V
PGND	Low-side driver ground vs. logic ground	V _{CC} = 14 V	-7 to 7	V
V _{VCC-PGND}	Logic supply vs. low-side driver ground		-0.3 to 21	V
V _{VCCL}	Regulated low-side driver supply vs. logic ground		-0.3 to 14	V
V _{LS}	Regulated low-side driver supply voltage ^{(4) (5) (6)}		-0.3 to 7	V
I _{LS-OUT}	Low-side regulator maximum current ^{(4) (5)}	Internal and RONL average consumption ⁽⁶⁾	Self-limited	mA
V _{VCC-VCCL}	Maximum low-side dropout voltage		-0.3 to self-regulated	V
V _{GL}	Low-side gate to PGND voltage	DC values	-0.3 to VCCL+0.3	V
V _{RONL}	Low-side turn-on resistor pin max. voltage		(GL-0.3V) to (VCCL+0.3V)	V
V _{BOOT}	BOOT pin voltage referred to GND		-0.3 to 621	V
V _{BO}	High-side regulator input voltage ^{(7) (5)}		-0.3 to 21	V
V _{HS}	Regulated high-side driver supply voltage ^{(7) (5)}		-0.3 to 7	V
I _{HS-OUT}	High-side regulator maximum current ^{(7) (5) (6)}	Internal and RONH average consumption ⁽⁶⁾	Self-limited	mA
V _{BOOT-VCCH}	Maximum high-side dropout voltage		-0.3 to self-regulated	V
V _{GH}	High-side gate to OUTb voltage ⁽⁷⁾		-0.3 to VCCH+0.3	V
V _{RONH}	High-side turn-on resistor pin max. voltage		(GH-0.3V) to (VCCH+0.3V)	V
R _{BOOT}	Minimum external bootstrap diode series resistance (if present)		2.7	Ω
dV _{OUT} /dt	Maximum OUT voltage slew rate ⁽¹⁾		120	V/ns
CIN	Comparator input voltage		-0.3 to 21	V
V _{in}	Logic inputs voltage range (LIN, HIN, $\overline{\text{SD}}$ /OD, STBY, FLT)		-0.3 to 21	V

Symbol	Parameter	Test condition	Value	Unit
I_{FLT}	Maximum $\overline{FLT}$ pin current (DC inward)	VCC = 7.0 V	10	mA
I_{OD}	Maximum $\overline{SD}/OD$ pin current (DC inward)	VCC = 12.0 V	10	mA
T_J	Junction temperature		-40 to 150	°C
T_{stg}	Storage temperature		-55 to 150	°C
ESD	HBM (Human Body Model)	ANSI/ESDA/JEDEC JS-001-2017	2	kV
	CDM (Charged Device Model)	ANSI/ESDA/JEDEC JS-002-2018	1	kV

1. Range estimated by characterization on a limited number of samples, not tested in production.
2. T_{CB} is the temperature of the case-exposed pad.
3. Value specified by design factor, pulse duration limited to 10 μ s and junction temperature.
4. PGND internally connected to SENSE.
5. $V_{LS} = V_{VCCCL-PGND}$, $V_{HS} = V_{VCCCH-OUTb}$, $V_{BO} = V_{BOOT-OUTb}$.
6. The internal low-side and high-side voltage regulators are not intended to be connected to external load or voltage sources.
7. OUTb internally connected to OUT.

4.2 Recommended operating conditions

All voltages referred to ground pins unless otherwise specified. The junction temperature must be maintained within recommended operating conditions with proper thermal design.

Table 3. Recommended operating conditions

Symbol	Parameter	Note	Min.	Max.	Unit
VCC	Logic supply voltage		10.7	18	V
V _{VCC-PGND}	Logic supply voltage vs, PGND		7.5	18	V
PGND	Low-side driver ground		-3	3	V
V _{BO}	V _{BOOT-OUTb} pin voltage		7.5	20	V
VS	Bus supply voltage		0	520	V
V _{OUT}	OUT pin voltage		-9.3 ⁽¹⁾ ⁽²⁾		V
VCCL	Low-side driver voltage vs. GND		3		V
V _{BOOT}	BOOT to GND voltage	⁽³⁾	0	540	V
CIN	Comparator input voltage		0	15	V
V _i	Logic inputs voltage range		0	20	V
R _{RONL} , R _{RONH}	External RON resistors		0	500	Ω
C _{VCCCH} , C _{VCCL}	Driver supply voltage bypass capacitors ⁽⁴⁾		47	220	nF
C _{BO}	High-side driver linear regulator input capacitors ⁽⁵⁾		C _{VCCCH}	3300	nF
C _{GMH} , C _{GML}	External gate capacitance		680	1800	pF
t _{DT}	Suggested minimum deadtime ⁽⁶⁾		300		ns
t _{INmin}	Minimum duration of input pulse		600		ns
f _{sw}	Switching frequency	Duty cycle = 50%		200 ⁽²⁾	kHz
T _{J-op}	Junction temperature		-40	125	°C

1. V_{BO} = 20 V, VCC = 10.7 V
2. The actual limit depends on power dissipation constraints.
3. BOOT must be ≥ 5V to propagate high-side commands.
4. X7R, 16V, ceramic capacitor having ESR lower or equal to 50 mΩ.
5. X7R, 50V, ceramic capacitor having ESR lower or equal to 50 mΩ.
6. Minimum value with minimum C_{GMX}.

4.3 Thermal data

Table 4. Thermal data

Symbol	Parameter	Value	Unit
R _{th(J-CB)}	Thermal resistance junction to each GaN transistor exposed pad	1.9	°C/W
R _{th(J-A)}	Thermal resistance junction-to-ambient ⁽¹⁾	17.8	°C/W

1. The junction to ambient thermal resistance is obtained simulating the device mounted on a 2s2p (4 layer) FR4 board as JESD51-5,7 with 6 thermal vias for each exposed pad. Power dissipation uniformly distributed over the two GaN transistors.

5 Electrical characteristics

Testing conditions: $T_J = 25\text{ }^{\circ}\text{C}$, $V_{CC} = V_{BO} = \overline{SD}/\overline{OD} = \overline{STBY} = 12\text{ V}$; $\overline{FLT} = \text{floating}$;
 $RONL = VCCL$; $RONH = VCCH$, $SENSE = CIN = PGND = 0\text{ V}$; $VS = 0\text{ V}$;
 $C_{VCCH} = C_{VCCL} = 47\text{ nF}$ (X7R, 16 V), $C_{BO} = 220\text{ nF}$ (X7R, 50 V).
All voltages referred to GND, unless otherwise specified.

Table 5. Electrical characteristics

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
GaN power transistor - electrical characteristics						
V _{(BR)DS_H}	Drain to source blocking voltage	VS to OUT, DC voltage I _{DSS} < 20 μA, GH = OUTb ⁽¹⁾	650			V
		VS to OUT, t _{PULSE} = 0.1 μs ⁽²⁾	750			
V _{GS(th)}	Gate to source threshold voltage	LIN = 3.3 V, SENSE = GND RONL = GL = 10 kΩ to OUT, I _{OUT-SENSE} = 2.5 mA		1.7		V
		HIN = 3.3 V, OUT = GND, RONH = GH = 10 kΩ to VS, I _{VS-OUT} = 2.5 mA				
I _{DSS}	Zero gate voltage drain current	V _{VS-OUT} = 600 V, GH = OUTb		0.45	20	μA
		V _{OUT-SENSE} = 600 V, GL = PGND				
I _{GS}	Gate to source current	V _{VS-OUT} = 0 V, RONH = GH OUT = GND, V _{GH-OUTb} = 6 V		60		μA
		V _{OUT-SENSE} = 0 V, RONL = GL V _{GL-PGND} = 6 V				
R _{DS(on)}	Drain to source on-state resistance	I _{OUT-SENSE} / I _{VS-OUT} = 3.2 A		138	190	mΩ
		I _{OUT-SENSE} / I _{VS-OUT} = 3.2 A		270		
		T _J = 125 °C ⁽²⁾				
GaN power transistor – characterization values						
Q _G	Total gate charge	V _{GS} = 0 to 6 V V _{DS} = 400 V ⁽²⁾		2.8		nC
Q _{OSS}	Output charge	V _{GS} = 0 V		24		nC
E _{OSS}	Output capacitance stored energy	V _{DS} = 400 V		3.5		μJ
C _{OSS}	Output capacitance	f = 100 kHz ⁽²⁾		30		pF
C _{O(ER)}	Effective output capacitance energy related	V _{GS} = 0 V		43		pF
C _{O(TR)}	Effective output capacitance time related	V _{DS} = 0 to 400 V ⁽²⁾		60		pF
Q _{RR}	Reverse Recovery Charge			0		nC
I _{RRM}	Reverse Recovery Current			0		A
V _{plat}	Gate plateau voltage	V _{DS} = 400 V, I _D = 1.6 A		2		V
V _{SD}	Source-drain reverse voltage	V _{GS} = 0 V, I _S = 1.6 A		2.2		V

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
GaN power transistor – inductive load switching characteristics						
t_{on}	Hard turn-on time	$V_{VS} = 400\text{ V}$		100		ns
t_{fall}	V_{DS} hard turn-on fall time	$I_D = 1.6\text{ A}$		20		ns
SR_{fall}	V_{DS} hard turn-on slew rate	$R_{ONH} = R_{ONL} = 33\ \Omega$		12		V/ns
E_{on}	Hard turn-on switching losses	$C_{GMH} = C_{GML} = 680\text{ pF}$ See Figure 4 for definitions ⁽²⁾		42		μJ
t_{off}	Hard turn-off time	$V_{VS} = 400\text{ V}$		100		ns
t_{rise}	V_{DS} hard turn-off rise time	$I_D = 1.6\text{ A}$		30		ns
SR_{rise}	V_{DS} hard turn-off slew rate	$C_{GMH} = C_{GML} = 680\text{ pF}$		8		V/ns
E_{off}	Hard turn-off switching losses	See Figure 4 for definitions ⁽²⁾		3		μJ
Logic section supply						
V_{CCthON}	VCC UVLO turn-ON threshold		9.5	10.0	10.6	V
$V_{CCthOFF}$	VCC UVLO turn-OFF threshold		9.0	9.5	10.1	V
V_{CChys}	VCC UV hysteresis		0.3	0.5	0.7	V
I_{QVCC}	VCC quiescent supply current	$\overline{STBY} = \overline{SD}/OD = 5\text{ V}$ $LIN = HIN = 0\text{ V}, V_{BO} = 15\text{ V}$		900	1200	μA
		$LIN = \overline{STBY} = \overline{SD}/OD = 5\text{ V}$ $HIN = 0\text{ V}, V_{BO} = 15\text{ V}$		1080	1450	μA
I_{QVCCU}	VCC undervoltage quiescent supply current	$V_{CC} = 7.0\text{ V}$		570	760	μA
I_{SBVCC}	VCC standby supply current	$\overline{STBY} = 0\text{ V}, BOOT = 10\text{ V}$		500	650	μA
I_{SVCC}	VCC switching supply current ⁽²⁾	$\overline{STBY} = \overline{SD}/OD = 5\text{ V}$ $V_{BO} = 15\text{ V}, V_{OUT} = V_{VS} = 0\text{ V}$ $LIN = \neg HIN, f_{SW} = 50\text{ kHz}, D = 50\%$ $C_{GMH} = C_{GML} = 680\text{ pF}$		1.55		mA
R_{BLEED}	Low-side gate bleeder	$V_{CCL} = V_{CC} = 0\text{ V}$ $PGND = GND, V_{GL} = 0.1\text{ V}$	75	100	125	k Ω
$t_{startup}$	VCC startup time from VCC = 10.5 V to GL = on	$LIN = \overline{STBY} = \overline{SD}/OD = 5\text{ V}$ $HIN = 0\text{ V}$			12	μs
Gate driver voltage regulators VCCL (V_{LS}) and VCCH (V_{HS})						
V_{HS} V_{LS}	VCCx regulator output voltage	$I_{VCCx} < 10\text{ mA}_{DC}$	5.55	6.00	6.45	V
		$T_J = -40\text{ }^\circ\text{C to } +125\text{ }^\circ\text{C}$ ⁽²⁾	5.4		6.6	V
V_{HStHON} V_{LStHON}	VCCx UVLO turn-on voltage		4.45	4.80	5.15	V
		$T_J = -40\text{ to } +125\text{ }^\circ\text{C}$ ⁽²⁾			5.25	V
$V_{HStHOFF}$ $V_{LStHOFF}$	VCCx UVLO turn-off voltage		4.30	4.65	4.95	V
		$T_J = -40\text{ to } +125\text{ }^\circ\text{C}$ ⁽²⁾	4.2			V
V_{HStHYS} V_{LStHYS}	VCCx UVLO hysteresis		0.15	0.2	0.23	V
V_{DROP_H}	VCCH regulator drop-out voltage	$BOOT = 12\text{ V}, OUT = 6\text{ V}, I_{VCCH} = 10\text{ mA}$			0.6	V

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
High-side driver section						
I_{QBO}	V_{BO} quiescent supply current	$\overline{STBY} = \overline{SD/OD} = 3.3\text{ V}$ $LIN = HIN = 0\text{ V}$, $V_{BO} = 12\text{ V}$		240	340	μA
		$HIN = \overline{STBY} = \overline{SD/OD} = 3.3\text{ V}$ $LIN = 0\text{ V}$, $V_{BO} = 12\text{ V}$		330	460	μA
I_{SBO}	V_{BO} switching supply current ⁽²⁾	$\overline{SD/OD} = \overline{STBY} = 3.3\text{ V}$ $VS = 0$, $V_{BOOT} = 12\text{ V}$ $HIN\ f_{SW} = 50\text{ kHz}$ $C_{GMH} = C_{GML} = 680\text{ pF}$		0.8		mA
$t_{HSstart}$	High-side startup time	$D_{BOOT} = STTH1R06$, $R_{BOOT} = 2.7\ \Omega$ from $LIN = 3.3\text{ V}$ to $V_{HS} > 5.1\text{ V}$			5	μs
I_{LK}	Driver high-voltage leakage current	$BOOT = OUT = 600\text{ V}$			11	μA
R_{DBOOT}	Bootstrap diode on resistance	$LIN = \overline{STBY} = \overline{SD/OD} = 3.3\text{ V}$ $HIN = 0\text{ V}$, $V_{VCC-BOOT} = 0.5\text{ V}$		120	140	Ω
Logic inputs and timings						
V_{ih}	High level logic threshold voltage	$T_J = 25\text{ }^\circ\text{C}$	2.0	2.27	2.5	V
		$T_J = -40\text{ to }+125\text{ }^\circ\text{C}$ ⁽²⁾			2.7	V
V_{il}	Low level logic threshold voltage	$T_J = 25\text{ }^\circ\text{C}$	1.1	1.31	1.45	V
		$T_J = -40\text{ to }+125\text{ }^\circ\text{C}$ ⁽²⁾	0.8			V
V_{ihys}	Logic input threshold hysteresis		0.7	0.96	1.2	V
V_{SSD}	SmartSD unlatch threshold	$T_J = 25\text{ }^\circ\text{C}$	0.5	0.65	0.8	V
		$T_J = -40\text{ to }+125\text{ }^\circ\text{C}$ ⁽²⁾			0.9	V
I_{INh}	LIN , HIN logic '1' input bias current	LIN , $HIN = 3.3\text{ V}$	15	22	36	μA
I_{INl}	LIN , HIN logic '0' input bias current	LIN , $HIN = 0\text{ V}$			1	μA
R_{PD_IN}	LIN , HIN pull-down resistor	LIN , $HIN = 3.3\text{ V}$	90	150	220	$\text{k}\Omega$
I_{SDh}	$\overline{SD/OD}$ logic '1' input bias current	$\overline{SD/OD} = 3.3\text{ V}$	7	10	15	μA
I_{SDl}	$\overline{SD/OD}$ logic '0' input bias current	$\overline{SD/OD} = 0\text{ V}$			1	μA
R_{PD_SD}	$\overline{SD/OD}$ pull-down resistor	$\overline{SD/OD} = 3.3\text{ V}$	220	330	450	$\text{k}\Omega$
R_{ON_OD}	$\overline{SD/OD}$ on-resistance	$\overline{SD/OD} = 400\text{ mV}$,	25	40	58	Ω
I_{OL_SD}	$\overline{SD/OD}$ low level sink current	$CIN = 2\text{ V}$	7	10	16	mA
t_{OD_fall}	$\overline{SD/OD}$ loaded fall time	$C_L = 10\text{ nF}$, $R_{PU} = 10\text{ k}\Omega$ to 5 V 90% to 10% $\overline{SD/OD}$		0.75		μs
I_{STBYh}	$\overline{STBY}$ logic '1' input bias current	$\overline{STBY} = 3.3\text{ V}$	7	10	15	μA
I_{STBYl}	$\overline{STBY}$ logic '0' input bias current	$\overline{STBY} = 0\text{ V}$			1	μA
R_{PD_STBY}	$\overline{STBY}$ pull-down resistor	$\overline{STBY} = 3.3\text{ V}$	220	330	450	$\text{k}\Omega$
R_{ON_FLT}	$\overline{FLT}$ on-resistance	$V_{FLT} = 400\text{ mV}$, $V_{CC} = 12\text{ V}$	60	80	135	Ω
		$V_{FLT} = 400\text{ mV}$, $V_{CC} = 3.3\text{ V}$	90	145	200	Ω
I_{OL_FLT}	$\overline{FLT}$ low level sink current	$V_{FLT} = 400\text{ mV}$	3	5	7	mA
I_{FLTh}	$\overline{FLT}$ high level bias current (when off)	$V_{FLT} = 3.3\text{ V}$			1	μA

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
I_{FLT}	$\overline{FLT}$ low level bias current (when off)	$V_{FLT} = 0\text{ V}$			1	μA
$V_{VCC-FLT}$	Min VCC voltage forcing $\overline{FLT}$ low				3.3	V
t_{Don}	LIN/HIN to GL/GH gate driver turn-on propagation delay	LIN or HIN = 0 V to 3.3 V, $C_{GMx} = 0\text{ pF}$	40	55	70	ns
t_{Doff}	LIN/HIN to GL/GH gate driver turn-off propagation delay	LIN or HIN = 3.3 V to 0 V, $C_{GMx} = 0\text{ pF}$	40	55	70	ns
t_{SDon}	$\overline{SD}/OD$ to Gx turn-on propagation delay	$\overline{SD}/OD = 0\text{ V to } 3.3\text{ V}$, $C_{GMx} = 0\text{ pF}$	45	65	100	ns
t_{SDoff}	$\overline{SD}/OD$ to Gx turn-off propagation delay	$\overline{SD}/OD = 3.3\text{ V to } 0\text{ V}$, $C_{GMx} = 0\text{ pF}$	40	65	100	ns
$t_{STBYoff}$	Standby to output turn-off propagation delay	$\overline{STBY} = 3.3\text{ V to } 0\text{ V}$, $C_{GMx} = 0\text{ pF}$	40	70	100	ns
t_{STBY}	Minimum time to enter low consumption	$\overline{STBY} = 3.3\text{ V to } 0\text{ V}$ ⁽²⁾	0.7		2	μs
$t_{STBY-FLT}$	Standby enters signaling to $\overline{FLT}$	$\overline{STBY} = 3.3\text{ V to } 0\text{ V}$ $\overline{FLT} = 10\text{ k}\Omega$ pull up to 5 V		1		μs
t_{WU}	Wake-up time from standby	$\overline{STBY} = 0\text{ V to } 3.3\text{ V}$, LIN = 3.3 V (Time from $\overline{STBY}$ rising to GL rising)			5	μs
t_{WU-FLT}	Standby end signaling to $\overline{FLT}$	$\overline{STBY} = 0\text{ V to } 3.3\text{ V}$, $\overline{FLT} = 10\text{ k}\Omega$ pull up to 5 V (Time from $\overline{STBY}$ rise to $V_{FLT} 1.8\text{ V}$)		3	5	μs
Comparator protection						
C_{INth}	Comparator threshold		350	400	450	mV
R_{PD_CIN}	CIN pull-down resistor	CIN = 1 V	75	100	125	k Ω
$t_{CIN-OUT}$	Comparator delay to half bridge output	CIN 0 V to 0.8 V, $C_{GMx} = 0\text{ pF}$ GH, GL 90%, $C_{GMx} = 0\text{ pF}$		180	230	ns
t_{CIN-OD}	Comparator delay to $\overline{SD}/OD$	CIN 0 V to 0.8 V $\overline{SD}/OD$ 90% (10 k Ω to 5 V, $C_{OD} = 0\text{ pF}$)		140	190	ns
$t_{CIN-FLT}$	Comparator delay to $\overline{FLT}$	CIN 0 V to 0.8 V: $\overline{FLT}$ 90% (10 k Ω to 5 V)		140	190	ns
$t_{CINfilter}$	Comparator input filter	CIN pulse 0 - 0.8 V	55	90	125	ns
Overtemperature Protection						
T_{TSD}	Shutdown temperature	⁽²⁾		175		$^{\circ}\text{C}$
T_{HYS}	Temperature hysteresis	⁽²⁾		20		$^{\circ}\text{C}$
t_{TSD}	Overtemperature protection enabling time	⁽²⁾ After $\overline{STBY} = \text{high}$			20	μs

1. Tested on wafer.

2. Not tested in production: value by characterization on a limited number of samples.

5.1 Characterization figures

Figure 4. Timing definitions

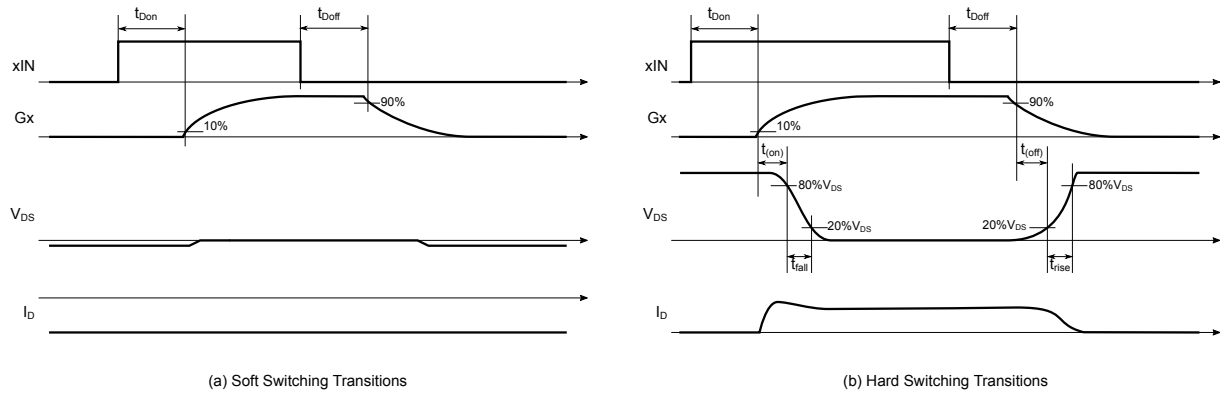


Figure 5. Typ I_D vs. V_{DS} at $T_J = 25^\circ\text{C}$

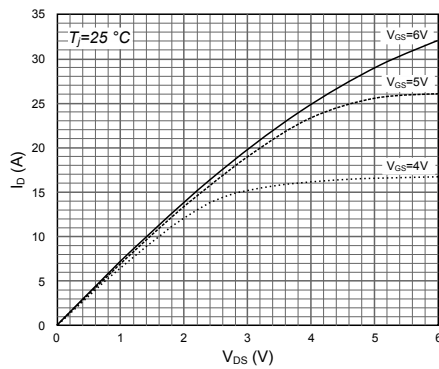


Figure 6. Typ I_D vs. V_{DS} at $T_J = 125^\circ\text{C}$

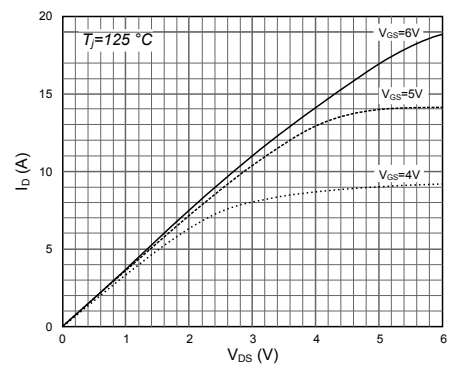


Figure 7. Typ I_S vs. V_{SD} at $T_J = 25^\circ\text{C}$

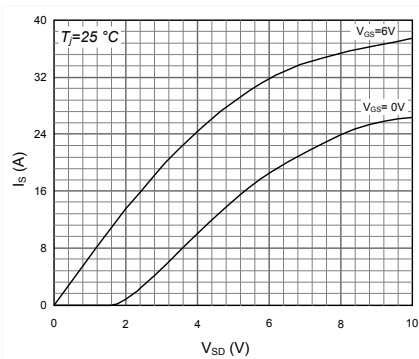


Figure 8. Typ I_S vs. V_{SD} at $T_J = 125^\circ\text{C}$

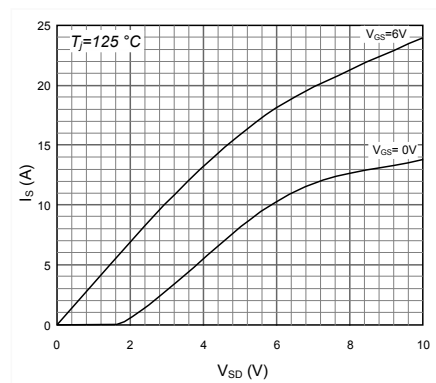


Figure 9. Typ I_D vs. V_{GS} at $T_J = 25\text{ °C}$

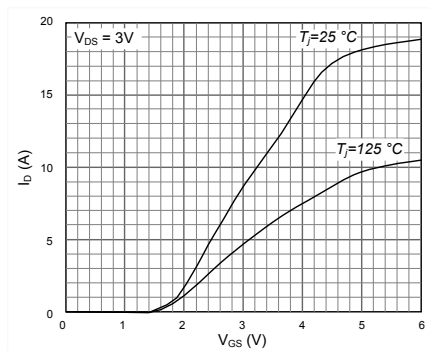


Figure 10. Typ $R_{DS(on)}$ vs. T_J normalized at 25 °C

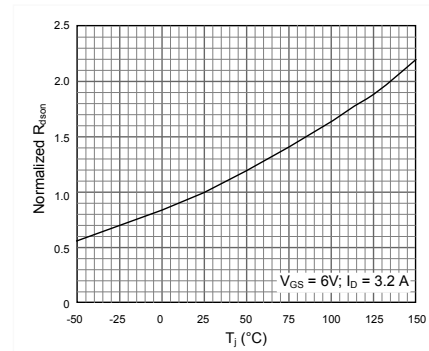


Figure 11. Typ Gate charge at $T_J = 25\text{ °C}$

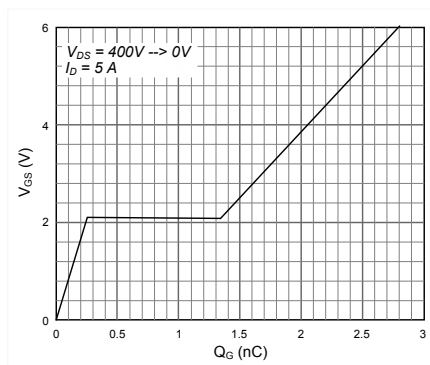
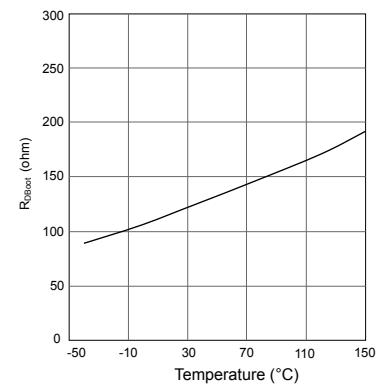


Figure 12. Typ R_{Dboot} vs. T_J

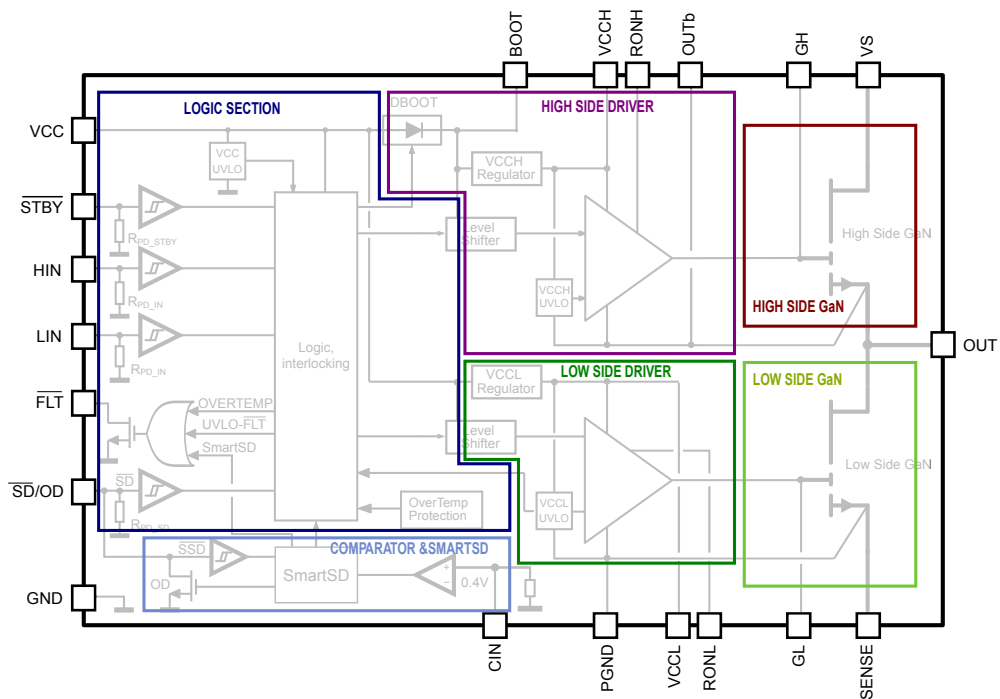


6 Device description

6.1 Device structure

Figure 13 is a simplified version of the block diagram of GANSPIN611. It consists of basic structures described in the following sections. Furthermore, GaN's gate terminal is externally accessible.

Figure 13. GANSPIN611 simplified block diagram



6.1.1 GaN power stage

The GaN transistors are the power switches that implement the switching stage of the power topology.

6.1.2 Logic section

This section receives the input signals, manages the system protection (UVLO, comparator and, gate driver overtemperature), and transfers the input pulses to relevant drivers through level shifters.

It is electrically referred to GND pin and supplied by VCC pin.

6.1.3 Comparator and smart shutdown

The embedded comparator, typically used for overcurrent detection, immediately turns off both GaN transistors, leaving the half-bridge in high impedance, once CIN input exceeds the threshold. The event is signaled to the $\overline{\text{SD/OD}}$ and $\overline{\text{FLT}}$ pins.

The smart shutdown (SmartSD) feature allows to automatically keep the switches off for the desired time to cool down the device.

6.1.4 Low-side driver

This block receives input pulses from the level shifter and provides driving action to the low-side GaN transistor.

It is electrically referred to PGND, which is connected to the Kelvin source connection of the low-side GaN transistor. Its input circuitry is supplied by VCC, while an integrated voltage regulator stabilizes the supply voltage of the output stage of the driver (V_{LS}). A UVLO comparator interrupts the half-bridge activity if the regulator's output voltage is insufficient for a proper GaN driving. A dedicated description of UVLO protection is described in the dedicated [Section 6.4.2](#).

A dedicated pin can be used to optionally increase turn-on resistance to lower hard-on dV/dt , while turn-off driving resistance is internally fixed.

The low-side driver has been designed to allow the use of current sense resistors without impacting the applied V_{GS} voltage.

6.1.5 High-side driver

This block receives input pulses from the logic section through the level shifter and provides driving action to the high-side GaN transistor.

It is electrically referred to OUTb, that is connected to the Kelvin source connection of the high-side GaN transistor. Its input circuitry is supplied by the voltage present at BOOT pin, while an integrated voltage regulator stabilizes the supply voltage of the output stage of the driver (V_{HS}). A UVLO comparator interrupts the high-side GaN activity if the regulator's output voltage is insufficient for a proper GaN driving. A dedicated description of UVLO protection is described in the dedicated [Section 6.4.4](#).

A dedicated pin can be used to optionally increase turn-on resistance to lower hard-on dV/dt , while turn-off driving resistance is internally fixed.

This section includes an equivalent bootstrap diode, synchronous with low-side on-time, that generates floating supply voltage (V_{BO}), starting from VCC voltage.

6.2 GaN transistors

The GANSPIN611 embeds two 650 V enhanced mode GaN transistors, connected in a half-bridge configuration. The technology of the embedded GaN transistors does not need bipolar driving: for this reason, negative voltage to turn off the transistor is not necessary.

The low-side GaN transistor is electrically connected between the OUT pin set (drain) and SENSE pin set (source): the SENSE exposed pad also represents a thermal buffer for this transistor. A suitable copper area is required to dissipate the power losses generated during normal operation.

The high-side GaN transistor is electrically connected between VS pins (drain) and OUT pins (source): the OUT exposed pad also represents a thermal buffer for this transistor. As suggested for low-side connection, a suitable copper area is required to dissipate the power losses generated during normal operation.

The embedded GaN transistors do not have intrinsic body diode and, consequently, exhibit zero reverse recovery losses. Nevertheless, the reverse conduction is permitted both during on-state and during off-state. Anti-parallel diodes are not required for proper functionality of the GANSPIN611 in both resonant and hard switching operation.

6.3 Truth table and control inputs

The GANSPIN611 has four logic inputs to control the embedded high-side and low-side power transistors.

- LIN: low-side driver input, active high;
- HIN: high-side driver input, active high.
- $\overline{STBY}$: standby input, active low;
- $\overline{SD/OD}$: shutdown input, active low.

An open-drain output is there ($\overline{FLT}$) to communicate externally the operating status of the device. For a proper level of this function, the VCC must be higher than $V_{VCC-FLT}$.

The $\overline{SD/OD}$ pin is also used as an output for the comparator with SmartSD disable time function (see [Section 6.6](#)).

[Table 6](#) summarizes the different IC operating modes depending on the input pin configurations.

Output pin configuration and IC consumption are also reported.

Table 6. Truth table

Mode	INPUTS				OUTPUTS			
	$\overline{\text{STBY}}$	$\overline{\text{SD/OD}}$	LIN	HIN	OUT	GL	GH	$\overline{\text{FLT}}$
Standby	L	X	X	X	High-Z	L	L	L
Shutdown	H	L	X	X	High-Z	L	L	H
High-Z	H	H	L	L	High-Z	L	L	H
Low-side on	H	H	H	L	L	H	L	H
High-side on	H	H	L	H	H	L	H	H
Interlocking	H	H	H	H	High-Z	L	L	H
Overcurrent	H	L ⁽¹⁾	X	X	High-Z	L	L	L

1. Forced low from the internal open-drain when $\text{CIN} > \text{CIN}_{th}$.

The logic inputs have internal pull-down resistors to set a defined logic level even in case of high impedance on signal lines. As a result, the transistors are set to off in the case of unconnected input pins.

The front-end of logic inputs consists of a comparator having a fixed threshold and defined hysteresis to ensure precise and robust level detection. The input pins can accept an input voltage up to 20 V independently from the VCC voltage level.

Propagation delays between LIN and HIN input pins to the transistor's gate are matched to obtain the best symmetry and minimum pulse width distortion.

The minimum duration of the pulse that can be transferred from LIN and HIN to the transistor gate is longer than t_{INmin} ; shorter pulses may be blanked.

If a remote controller or monitoring unit can exploit the $\overline{\text{FLT}}$ function, a pull-up current or an external resistor ($R_{PU_FLT_{ext}}$) is required to properly detect the activation of the internal open-drain unit. In this case, the high-level voltage can be set to a maximum level of 20 V independently from VCC. When unused, this pin must be connected to GND.

The $\overline{\text{STBY}}$ pin is intended to activate standby mode to reduce the IC consumption during long-lasting inactive times or between burst modes. The description of this mode is reported in [Section 6.5](#).

6.4 Supply rails, LDOs, UVLO protections, and bootstrap diode

The GANSPIN611 is supplied by two rails: VCC, referred to GND, and BOOT referred to OUTb.

Integrated LDOs generate supply voltages for low-side and high-side output stages (V_{LS} and V_{HS}). Undervoltage circuitries monitor VCC, V_{LS} and V_{HS} .

An integrated bootstrap diode is there to generate floating supply voltage for the high-side structure.

6.4.1 VCC supply structure and relevant UVLO protection

The VCC pin supplies the logic circuit, the input structure of the low-side driver, and the integrated bootstrap structure (D_{BOOT}). Low-ESR ceramic capacitors must be connected as close as possible between VCC and GND (100 nF typ., X7R, 50 V).

Undervoltage protection is available on the VCC supply pin. A hysteresis sets the turn-off threshold.

When VCC voltage reaches the V_{CCthON} threshold, the device enters normal operation: if V_{LS} is above UVLO level and the $\overline{\text{STBY}}$ pin is high, the $\overline{\text{FLT}}$ pin is released and the device sets drivers output according to actual input pins.

When VCC voltage goes below the $V_{CCthOFF}$ threshold, both high-side and low-side gate driver outputs are forced low and the $\overline{\text{FLT}}$ pin is forced low to signal the state to remote controllers.

6.4.2 V_{LS} supply structure and relevant UVLO protection

The integrated VCCL regulator is fed by VCC voltage to stabilize the low-side driver output terminal (VCCL, referred to PGND or, shortly $V_{LS} = 6\text{ V typ.}$).

Low-ESR ceramic capacitors must be connected as close as possible between VCCL and PGND (C_{VCCL} recommended value is 100 nF, X7R, 16 V) to obtain a clean supply voltage.

An undervoltage protection is available on the V_{LS} supply voltage that bias the low-side driver output stage. When V_{LS} voltage reaches the V_{LSthON} threshold, the device enables the low-side driver normal operation. When V_{LS} voltage goes below the $V_{LSthOFF}$ threshold, both high-side and low-side gate driver outputs are forced low and the $\overline{FLT}$ pin is forced low to signal this condition to the remote controllers.

6.4.3 Bootstrap diode

The GANSPIN611 integrates a bootstrap diode structure connected between the VCC and BOOT pins, to supply the high-side floating supply voltage $V_{BOOT-OUTb}$ (or shortly V_{BO}). A very low ESR ceramic capacitor (C_{BOOT} to be selected between 100 nF and 3.3 μ F, X7R, 50 V) must be placed as close as possible between the BOOT and OUT pins.

The bootstrap DC characteristics are detailed in [Figure 12](#).

The final voltage drop between VCC and V_{BO} depends on multiple factors like duty cycle, operating frequency, GaN gate charge, GaN leakage, temperature, etc. In case the voltage on V_{BO} is not sufficient for a proper VCCH regulator operation, either increasing the VCC value or using an external bootstrap diode can obtain a correct V_{BO} voltage.

A resistor $R_{BOOT} \geq 2.7 \Omega$ must be placed in series with the above mentioned external bootstrap diode to limit the amount of peak charging current flowing into the internal connection between OUTb and OUT.

6.4.4 V_{HS} supply structure and relevant UVLO protection

The integrated VCCH regulator is connected to the V_{BO} voltage to stabilize the high-side driver output terminal (VCCH, referred to OUTb or, shortly, $V_{HS} = 6 \text{ V typ.}$).

The high-side LDO is equipped with fast startup turn-on circuitry to minimize the wake-up time especially during intermittent operation (burst mode).

Low-ESR ceramic capacitors must be connected as close as possible between VCCH and OUTb (C_{VCCH} recommended value is 100 nF, X7R, 16 V) to obtain a clean supply voltage.

An undervoltage protection is available on the V_{HS} supply voltage that bias the high-side driver output stage (VCCH – OUTb).

When V_{HS} voltage reaches the V_{HSthON} threshold, the high-side driver is enabled to accept turn-on/off commands from the input logic block.

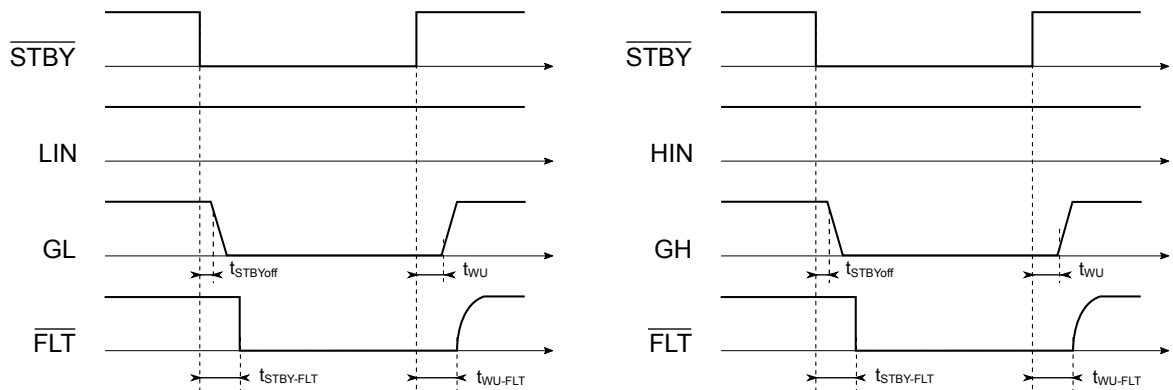
When V_{HS} voltage goes below the $V_{HSthOFF}$ threshold, the high-side gate driver output is forced low.

V_{HS} UVLO status is not signaled on the $\overline{FLT}$ pin and the low-side driver continues to operate according to inputs and other protections.

6.5 Standby

The GANSPIN611 is designed to reduce the current consumption of both the logic portion and low-side driver when the $\overline{STBY}$ pin is pulled to GND. Low-side and high-side output are immediately set low to leave the half-bridge in a 3-state, while the $\overline{FLT}$ pin is forced low, and consumption is reduced if the $\overline{STBY}$ pin is pulled to GND for at least t_{STBY} . The overtemperature and the comparator protections are disabled in this operating condition.

Setting the $\overline{STBY}$ pin high, the device wakes up and operation is restored: the $\overline{FLT}$ pin is released within t_{WU-FLT} while the driver's outputs are set according to inputs, providing that relevant UVLOs are not active, within t_{WU} .

Figure 14. Standby timings


6.6 Comparator with SmartSD

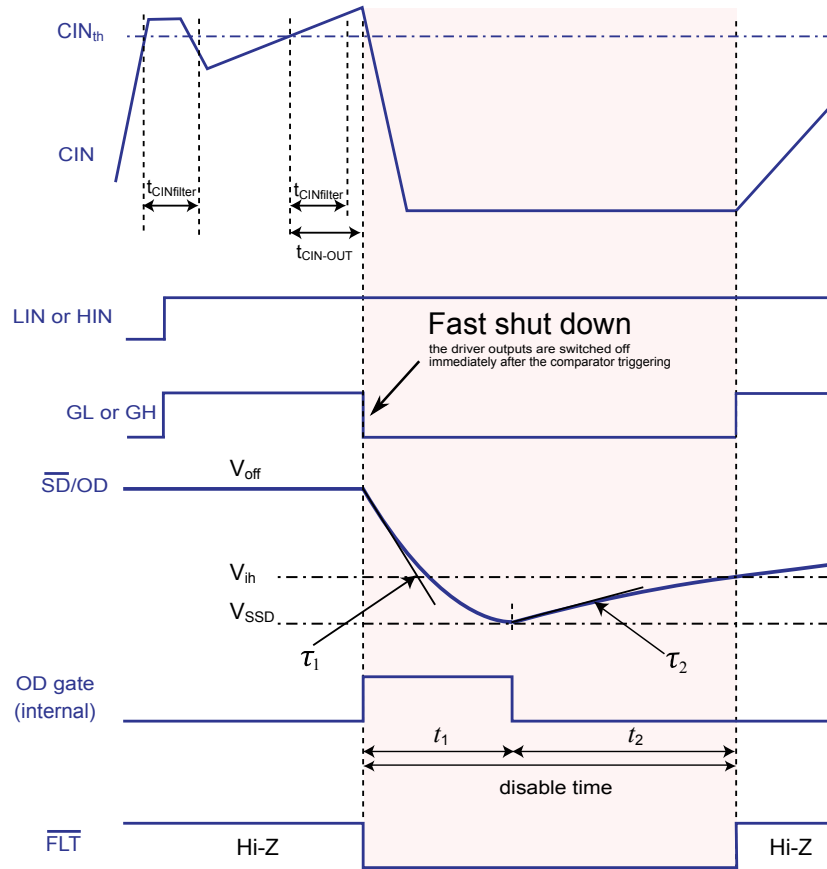
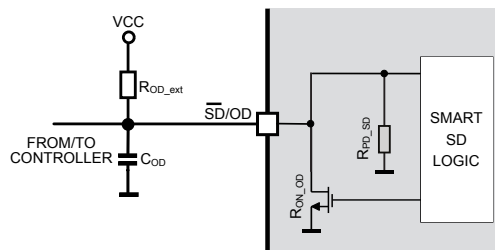
The GANSPIN611 integrates a comparator committed to the fault sensing function.

The comparator input can be connected to an external shunt resistor in order to implement a simple overcurrent detection function with an automatic OFF-time mechanism (Smart Shutdown) providing the possibility to increase the disable time after the fault event up to an arbitrary value without increasing the delay time of the protection.

The comparator has an internal voltage reference CIN_{th} connected to the inverting input, while the non-inverting input is available on the CIN pin. The output signal of the comparator is filtered from glitches shorter than $t_{\text{CINfilter}}$ and then fed to the Smart Shutdown logic.

The $\overline{\text{SD/OD}}$ is connected to a timing capacitor C_{OD} and a pull-up to determine the output disable time of the fault event.

When an overcurrent is detected, gates are immediately turned off, the $\overline{\text{FLT}}$ pin is forced low to signal the state to the controller, the $\overline{\text{SD/OD}}$ pin discharges C_{OD} down to V_{SSD} and then the external pull-up charges it again. Once C_{OD} reaches V_{ih} , the gate driving restarts and $\overline{\text{FLT}}$ is released.

Figure 15. Smart Shutdown timing waveforms

SMART SHUTDOWN CIRCUIT
 automatic off time


An approximation of the disable time is given by:

$$t_1 \cong \tau_1 \cdot \ln \left(\frac{V_{off} - V_{on}}{V_{SSD} - V_{on}} \right)$$

$$t_2 \cong \tau_2 \cdot \ln \left(\frac{V_{SSD} - V_{off}}{V_{ih} - V_{off}} \right)$$

Where:

$$\tau_1 = (R_{ON_OD} // R_{OD_ext}) \cdot C_{OD}$$

$$\tau_2 = (R_{PD_SD} // R_{OD_ext}) \cdot C_{OD}$$

$$V_{on} = \frac{R_{ON_OD}}{R_{ON_OD} + R_{OD_ext}} \cdot V_{BIAS}$$

$$V_{off} = \frac{R_{PD_SD}}{R_{PD_SD} + R_{OD_ext}} \cdot V_{BIAS}$$

6.7 Thermal shutdown

The GANSPIN611 provides a thermal shutdown protection feature to protect the gate driver from operating at abnormal temperature.

When, during active mode, the junction temperature reaches the T_{TSD} temperature threshold, the device turns the driver outputs off to leave the half-bridge in 3-state and signals this condition forcing the $\overline{FLT}$ pin low. The status of all the input pins is ignored.

When the junction temperature is lower than $T_{TSD}-T_{HYS}$, the device operation is restored and the $\overline{FLT}$ pin is released.

Since the temperature sensor is located on the driver-exposed pad EP1, temperature sensing of GaN transistors is typically not accurate: the temperature difference of the GaN exposed pad EP2 and EP3 depends on PCB layout and system cooling.

The overtemperature detection is inactive when the device is operating in standby mode to minimize consumption.

The overtemperature detection is inactive when the device is operating in standby mode or in VCC UVLO to minimize consumption. On standby mode exit or VCC UVLO exit, overtemperature requires t_{TSD} to protect against overtemperature.

7 PCB, BOM, and layout recommendations

7.1 PCB suggestions

This section lists some tips to facilitate the PCB routing of the GANSPIN611.

7.1.1 External BOM values selection and placement

A list of recommended value ranges for some key components are reported.

The bulk capacitors required for VCC, VCCL, VCCH, and BOOT must be placed as close as possible to relevant pins and relevant references. Such capacitors must be low ESR/ESL ceramic components having rated voltages that are almost twice the maximum operating voltages to overcome the well-known value modulation versus bias voltage.

The eventual external bootstrap diode, useful to reduce the high-side startup time, requires a series resistance larger than 2.7 Ω . In case an external bootstrap diode is used, the C_{BOOT} capacitor must be placed on the PCB in a way that the negative terminal is put as close as possible to the OUTb pin: this arrangement ensures that the charging current flows in the shortest track as possible. The lower the R_{BOOT} resistor, the lower high-side startup time but the higher diode recovery losses and EMI. To minimize high-side startup time is recommended to minimize C_{BOOT} and C_{VCCH}. A good trade-off to limit also VCCx ripple is to use C_{VCCH} = C_{VCCL} = 100 nF.

The gate capacitor C_{GMx}, must be adjacent to the GH to OUTb and GL to PGND pins.

The turn-on programming resistors, R_{ONL} and R_{ONH}, used to tune the hard-on dV/dt, must be placed very close to the relevant IC to minimize the length of the track connected to the RONx pin. If not used, a direct connection between the RONx pin and VCCx pin is required

Table 7. External BOM summary

Symbol	Function	Value (range)	Technology	Min. rating
C _{VCC}	VCC large bulk capacitor (it is normally used as bulk capacitor of controller too)	2.2 to 10 μ F	EL-Cap (or X7R)	25 V (50 V)
	VCC bypass capacitor	100 nF	X7R	50 V
C _{BOOT}	BOOT to OUTb bypass capacitor	C _{VCCH} to 3300 nF	X7R	50 V
C _{VCCL}	VCCL to PGND bypass capacitor	47 nF to 220 nF	X7R	16 V
C _{VCCH}	VCCH to OUT bypass capacitor	47 nF to 220 nF	X7R	16 V
R _{BOOT}	Current limiting resistor of external D _{BOOT}	$\geq 2.7 \Omega$		
D _{BOOT}	External bootstrap diode (if needed)	STTH1R06 or equivalent	Turbofast	600 V / 1 A
C _{GML}	GL to PGND gate capacitor	680 pF	X7R	16 V
C _{GMH}	GH to OUTb gate capacitor	680 pF	X7R	16 V
R _{ONx}	Turn-on resistors of LS and HS GaNs	0 Ω to 2 k Ω		

To speed-up start-up time, the user shall minimize C_{BOOT} and C_{VCCH}.

Most motor control applications (depending on gate load) are optimized when using C_{VCCx} = 100 nF and C_{BOOT} = 220 to 470 nF. A larger C_{BOOT} capacitor could be rarely required in specific applications if a very long high side on-time is required. On all other applications is recommended to keep C_{BOOT} small to avoid increasing start-up time, the potential need of the additional external bootstrap diode, the diode dissipation. In extreme cases, as in all gate driver applications, excessive C_{BOOT} and small C_{VCC} can lead to VCC drops due to charge sharing when low-side turns on, detected by the VCC UVLO.

PGND is internally connected to the SENSE pin: do not connect externally to any other GND or SENSE route.

OUTb is internally connected to the OUT pin: do not connect externally to the OUT route.

VCCL and VCCH are the output access to the internal voltage regulator: forcing these pins to external voltage regulators may result in unrecoverable damage of the IC.

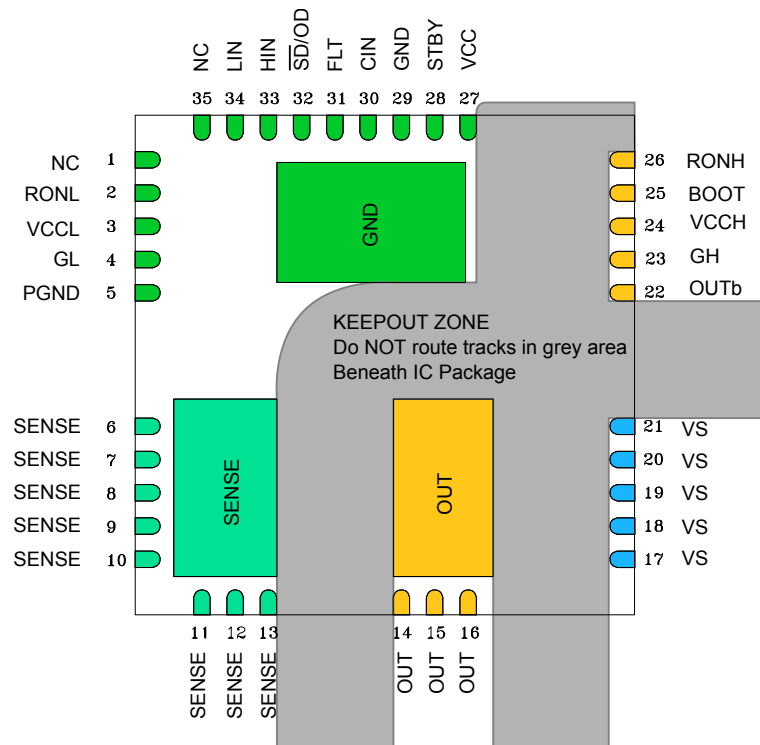
The GANSPIN611 has a comparator that, once connected CIN to the shunt resistor, can provide an effective programmable overcurrent protection.

A GND to PGND ground bounce noise could be present on an applicative board summing to the shunt voltage, determining spurious overcurrent intervention. We recommend using an RC filter on CIN pin to filter out this noise. The filtering capacitor shall be placed adjacent to CIN pin and on the same PCB side of the GANSPIN611 for maximum filtering effect.

7.1.2 Distances

The QNF9x9x1 package is designed to simplify the respect of the safety norms regarding creepage distances. The gray area depicted in Figure 16 represents the distances to maintain the creepages at PCB level. The pin sets are colored differently to represent the pins that are referred to the same voltage reference.

Figure 16. Keepout regions for safety



7.1.3 Noise reduction

To minimize the noise generation during normal operation of typical applications, a few simple steps can be followed:

1. Connect signal GND and power GND to a single star point. Signal ground consists of controller GND and signal GND of the GANSPIN611.
2. If a shunt resistor is necessary, this component should have very small ELS and be placed as close as possible to the GANSPIN611. A standard SMD shunt is typically suitable, but in the case of high current transients resulting in high di/dt , lower ESL could be required. A cheaper alternative to a low ESL resistor consists of the parallel of multiple smaller resistors (for example, 3x 0603 SMD resistors have similar ESL of a 1020 package shunt resistor and is much lower than a 2010 standard package).
3. To minimize parasitic capacitance and noise generation, it is preferable to route the OUT node very closely to the load minimizing the overlap with any other nets.
4. Components connected to BOOT, VCCH, RONH, and OUTb floats together with the OUT node. They must be placed as close as possible to the listed pins minimizing the overlap with other nets.
5. Keep current loops as small as possible. A high-voltage ceramic capacitor connected between high-voltage bus and power ground and placed as close as possible to the GANSPIN611 facilitates the reduction of such loops.
6. To increase thermal performance and maximum power, thermal vias could be used under SENSE and OUT exposed pads. However, keep the high-voltage power loop made with the VS ceramic capacitor as close and as small as possible to minimize stray inductance. Due to the intrinsic small capacitance of GaN and a VS high stray inductance, some oscillations could be observed after a di/dt transition. In such cases, adding a 1-2.2 Ω resistor in series to the GH/GL capacitance helps to dump those oscillations faster.

Heat generated by the IC can be dissipated using exposed pads:

1. SENSE and OUT exposed pads are intended to spread out the heat generated by the GaN during switching activity. The use of standard vias beneath the EPs helps to both transfer heat between different layers and minimize the risk of voids (air bubbles) between IC's exposed pads and PCB footprint. Keep the ground return track of the VS ceramic capacitor as close as possible to the device. Consider that the copper layer on the same side of the device is the most thermally efficient since vias add a resistive contribution on the thermal transfer.
2. The GND exposed pad dissipates only the gate driver power, which is typically low in the relatively low frequency hard switching applications (compared to the high frequency resonant applications). It is recommended to exploit PCB space to dissipate the OUT and SENSE exposed pads.
3. The VS pin set is not responsible for thermal dissipation: the net connected to this potential has to be sized for RMS current only.
4. High copper thickness (2 oz) improves the heat spreading and helps to transfer far from the IC. Smaller support thickness (for example, FR4 – 1 mm instead of 1.6 mm) helps to transfer the heat between copper layers, but care should be taken on parasitic capacitance generation and board robustness.

8 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

8.1 QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, package information

Table 8. QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, package dimensions

Symbol	Dimensions [mm]		
	Min.	Typ.	Max
A	0.90	0.98	1.05
A3	-	0.127	-
b	0.25	0.30	0.35
D	8.96	9.00	9.04
E	8.96	9.00	9.04
D1	3.30	3.40	3.50
E1	2.06	2.16	2.26
D2	1.76	1.86	1.96
E2	3.10	3.20	3.30
D3	1.70	1.80	1.90
E3	3.10	3.20	3.30
e	-	0.6 Ref	-
K	0.2	-	-
L	0.35	0.45	0.55
n ⁽¹⁾	35		
	TOLERANCE		
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		

1. n is the total number of terminals

Note: Dimensioning and tolerances conform to ASME Y14.5-2009.

Note: Dimensions do not include mold protrusion, not to exceed 0.15 mm.

Note: Package outline exclusive of metal burr dimensions.

BOTTOM VIEW



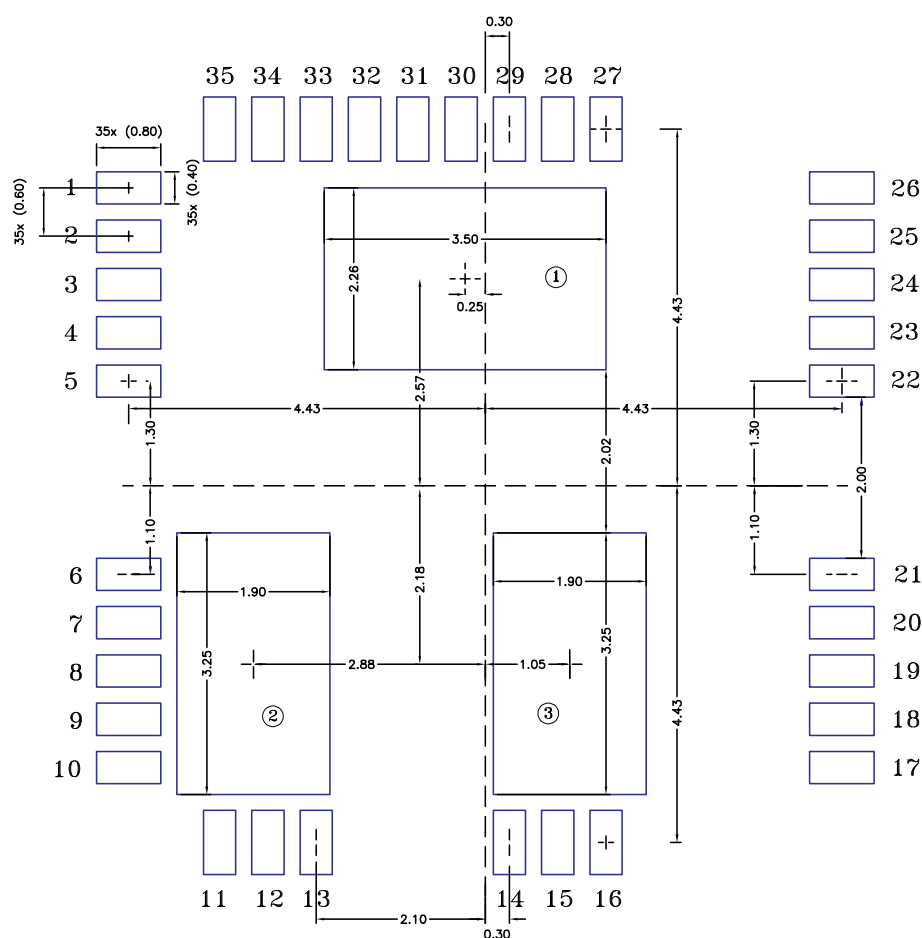
8.2 Suggested footprint

The GANSPIN611 footprint for the PCB layout is usually defined based on several design factors such as assembly plant technology capabilities and board component density. For easy device usage and evaluation, STMicroelectronics provides the following footprint design, which is suitable for the largest variety of PCBs.

The following footprint indicates the copper area that should be free from the solder mask, while the copper area could extend beyond the indicated areas especially for EP2 and EP3. To aid thermal dissipation, it is recommended to add, if possible, thermal vias under these EPADs to transfer and dissipate device heat to the other PCB copper layers.

A PCB layout example is available with the GANSPIN611 evaluation board.

Figure 18. QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, suggested footprint



9 Ordering information

Table 9. Order code

Order code	Package	Package marking	Packaging
GANSPIN611	QFN 9x9x1 mm	GSPIN611	Tray
GANSPIN611TR	QFN 9x9x1 mm	GSPIN611	Tape and Reel

Revision history

Table 10. Document revision history

Date	Version	Changes
26-Sep-2025	1	Initial release.

Contents

1	Block diagram	3
2	Typical application schematic	4
3	Pin descriptions	5
4	Electrical data	7
4.1	Absolute maximum ratings	7
4.2	Recommended operating conditions	9
4.3	Thermal data	9
5	Electrical characteristics	10
5.1	Characterization figures	14
6	Device description	16
6.1	Device structure	16
6.1.1	GaN power stage	16
6.1.2	Logic section	16
6.1.3	Comparator and smart shutdown	16
6.1.4	Low-side driver	16
6.1.5	High-side driver	17
6.2	GaN transistors	17
6.3	Truth table and control inputs	17
6.4	Supply rails, LDOs, UVLO protections, and bootstrap diode	18
6.4.1	VCC supply structure and relevant UVLO protection	18
6.4.2	V _{LS} supply structure and relevant UVLO protection	18
6.4.3	Bootstrap diode	19
6.4.4	V _{HS} supply structure and relevant UVLO protection	19
6.5	Standby	19
6.6	Comparator with SmartSD	20
6.7	Thermal shutdown	22
7	PCB, BOM, and layout recommendations	23
7.1	PCB suggestions	23
7.1.1	External BOM values selection and placement	23
7.1.2	Distances	25
7.1.3	Noise reduction	25
8	Package information	27
8.1	QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, package information	27
8.2	Suggested footprint	29



9	Ordering information	30
	Revision history	31
	List of tables	34
	List of figures.....	35

List of tables

Table 1.	GANSPIN611 pin list	5
Table 2.	Absolute maximum ratings	7
Table 3.	Recommended operating conditions.	9
Table 4.	Thermal data.	9
Table 5.	Electrical characteristics	10
Table 6.	Truth table	18
Table 7.	External BOM summary	23
Table 8.	QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, package dimensions	27
Table 9.	Order code	30
Table 10.	Document revision history	31

List of figures

Figure 1.	GANSPIN611 block diagram.	3
Figure 2.	Typical motor control application schematic	4
Figure 3.	GANSPIN611 pin connections	5
Figure 4.	Timing definitions	14
Figure 5.	Typ I_D vs. V_{DS} at $T_J = 25\text{ }^{\circ}\text{C}$	14
Figure 6.	Typ I_D vs. V_{DS} at $T_J = 125\text{ }^{\circ}\text{C}$	14
Figure 7.	Typ I_S vs. V_{SD} at $T_J = 25\text{ }^{\circ}\text{C}$	14
Figure 8.	Typ I_S vs. V_{SD} at $T_J = 125\text{ }^{\circ}\text{C}$	14
Figure 9.	Typ I_D vs. V_{GS} at $T_J = 25\text{ }^{\circ}\text{C}$	15
Figure 10.	Typ $R_{DS(on)}$ vs. T_J normalized at $25\text{ }^{\circ}\text{C}$	15
Figure 11.	Typ Gate charge at $T_J = 25\text{ }^{\circ}\text{C}$	15
Figure 12.	Typ R_{Dboot} vs. T_J	15
Figure 13.	GANSPIN611 simplified block diagram	16
Figure 14.	Standby timings	20
Figure 15.	Smart Shutdown timing waveforms	21
Figure 16.	Keepout regions for safety	25
Figure 17.	QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, package outline	28
Figure 18.	QFN 9 x 9 x 1 mm, 35 leads, 0.6 mm pitch, suggested footprint	29

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